



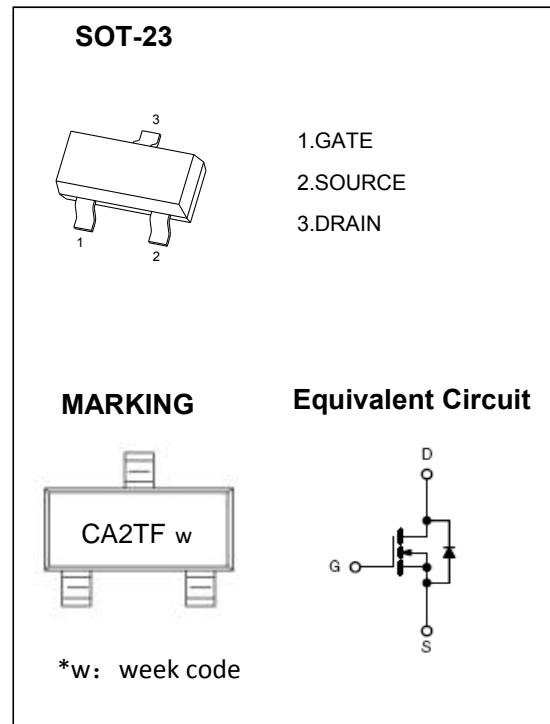
SHENZHEN TUOFENG SEMICONDUCTOR TECHNOLOGY CO.,LTD

# SOT-23 Plastic-Encapsulate MOSFETS

TF2310

## TF2310 N-Channel 60-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	$I_D$
60V	0.065Ω@ 10V	3.0 A
	0.075Ω@ 4.5 V	



## Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	3	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	10	A
Maximum Power Dissipation	$P_D$	1.20	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	73.5	°C/W
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## Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	65	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$



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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	60	65	-	V
Zero Gate Voltage Drain Current	$\text{I}_{\text{DSS}}$	$\text{V}_{\text{DS}}=60\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{GS}}=\pm20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
<b>On Characteristics</b> <small>(Note 3)</small>						
Gate Threshold Voltage	$\text{V}_{\text{GS}(\text{th})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	1.0	1.3	2.0	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=3\text{A}$		0.065	0.075	$\Omega$
		$\text{V}_{\text{GS}}=4.5\text{V}, \text{I}_D=2\text{A}$		0.075	0.085	$\Omega$
Forward Transconductance	$\text{g}_{\text{FS}}$	$\text{V}_{\text{DS}}=15\text{V}, \text{I}_D=2\text{A}$		3	-	S
<b>Dynamic Characteristics</b> <small>(Note 4)</small>						
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{DS}}=30\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{F}=1.0\text{MHz}$	-	247	-	PF
Output Capacitance	$\text{C}_{\text{oss}}$		-	34	-	PF
Reverse Transfer Capacitance	$\text{C}_{\text{rss}}$		-	19.5	-	PF
<b>Switching Characteristics</b> <small>(Note 4)</small>						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$\text{V}_{\text{DD}}=30\text{V}, \text{I}_D=1.5\text{A}$ $\text{V}_{\text{GS}}=10\text{V}, \text{R}_{\text{GEN}}=1\Omega$	-	6	-	nS
Turn-on Rise Time	$t_r$		-	15	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	15	-	nS
Turn-Off Fall Time	$t_f$		-	10	-	nS
Total Gate Charge	$\text{Q}_g$	$\text{V}_{\text{DS}}=30\text{V}, \text{I}_D=3\text{A}, \text{V}_{\text{GS}}=4.5\text{V}$	-	6	-	nC
Gate-Source Charge	$\text{Q}_{\text{gs}}$		-	1	-	nC
Gate-Drain Charge	$\text{Q}_{\text{gd}}$		-	1.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <small>(Note 3)</small>	$\text{V}_{\text{SD}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_s=1.0\text{A}$	-	0.77	1.2	V
Diode Forward Current <small>(Note 2)</small>	$\text{I}_s$		-	1.0	-	A

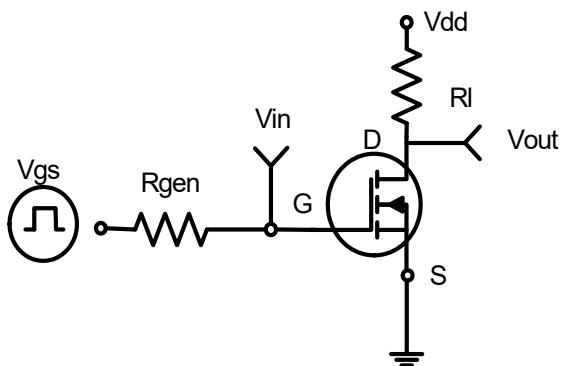
## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

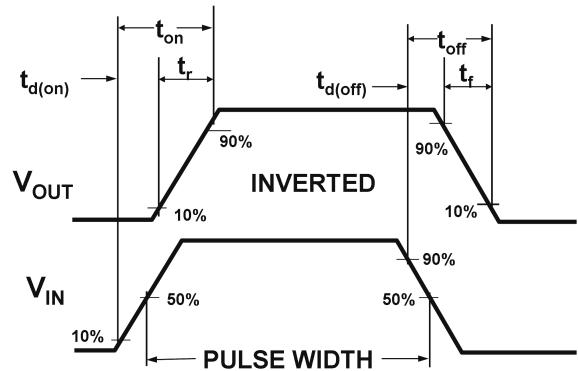
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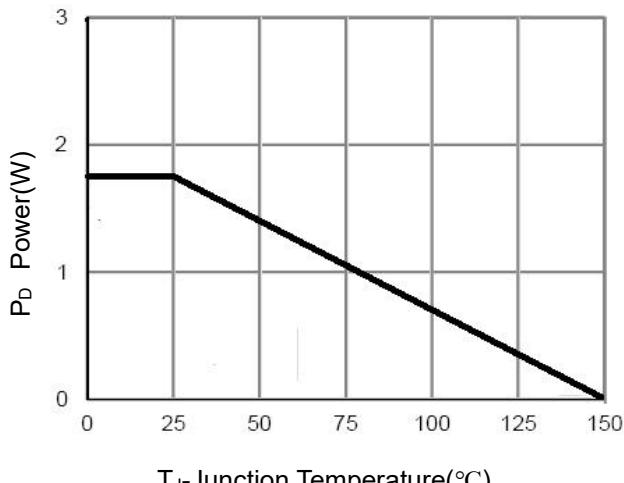
## Typical Electrical and Thermal Characteristics



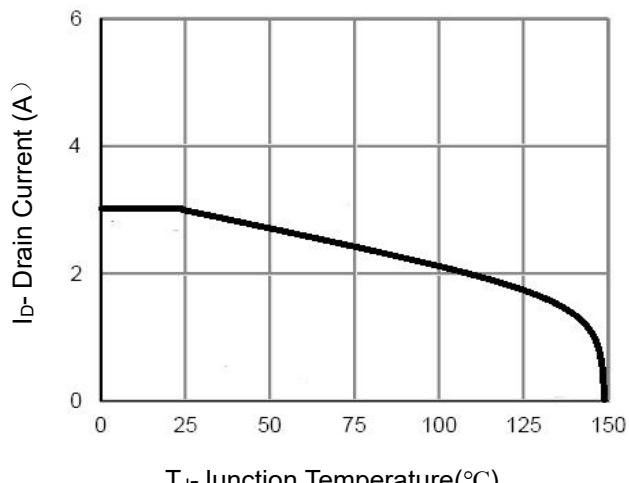
**Figure 1:Switching Test Circuit**



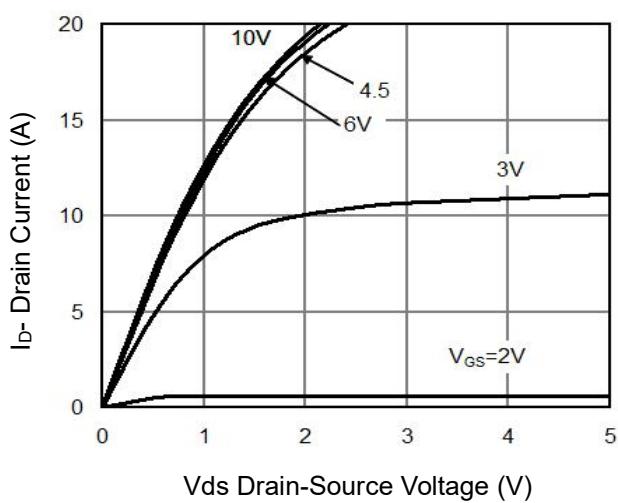
**Figure 2:Switching Waveforms**



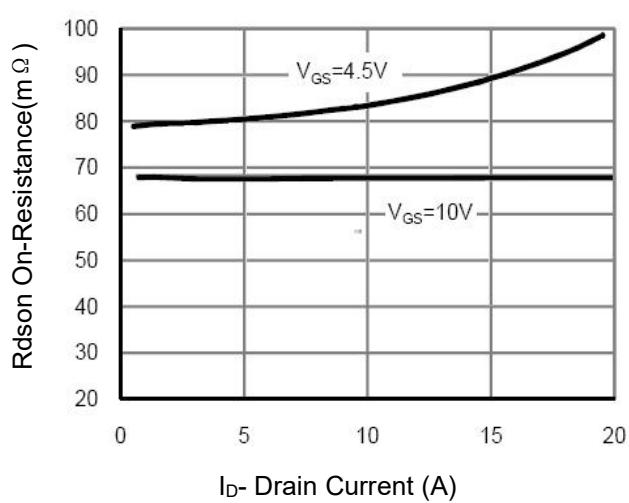
**Figure 3 Power Dissipation**



**Figure 4 Drain Current**



**Figure 5 Output Characteristics**



**Figure 6 Drain-Source On-Resistance**

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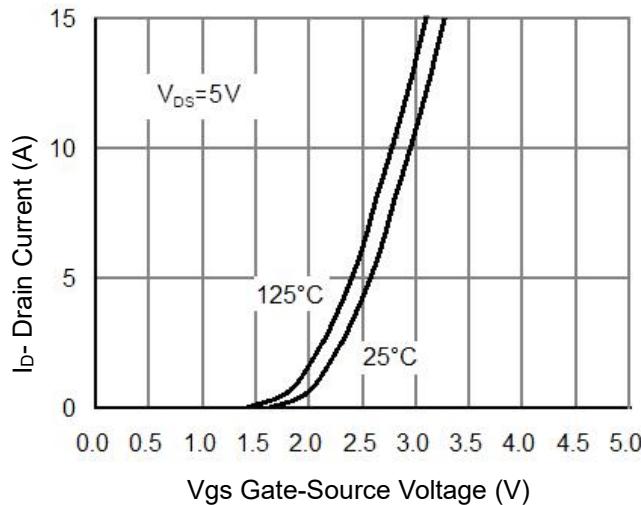


Figure 7 Transfer Characteristics

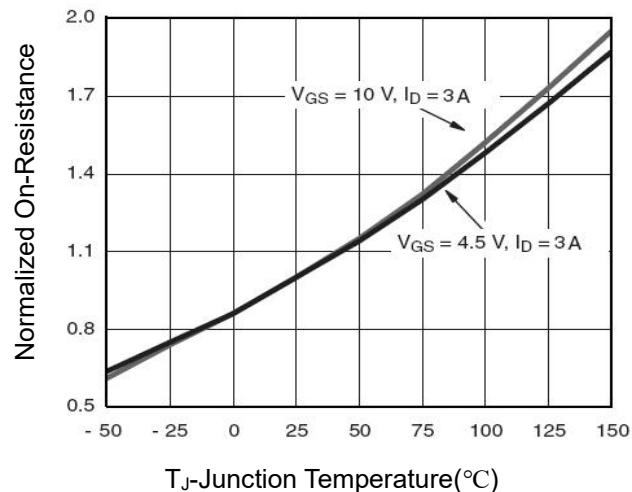


Figure 8 Drain-Source On-Resistance

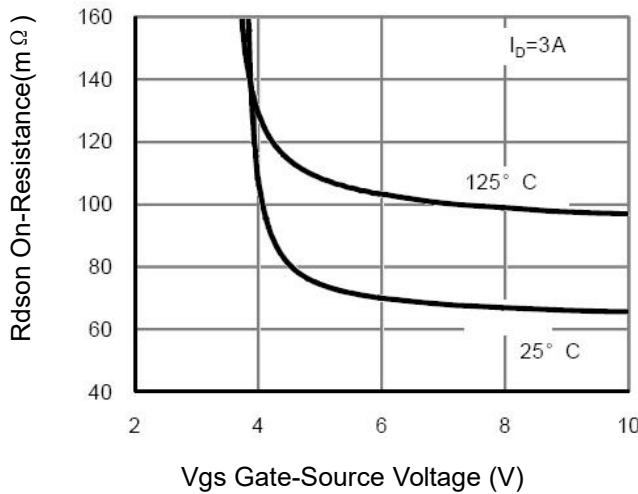


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

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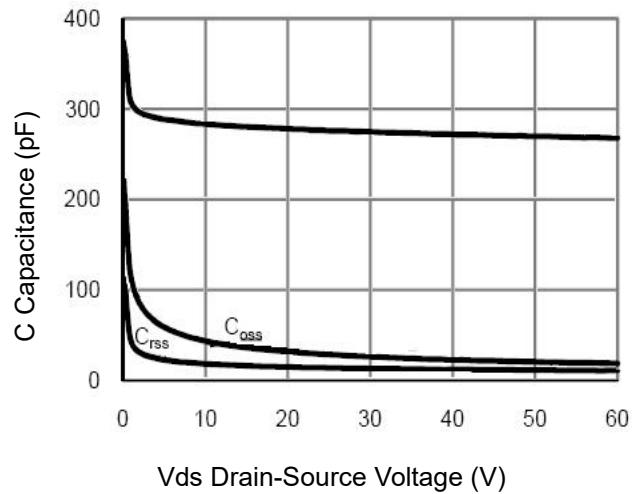


Figure 10 Capacitance vs  $V_{DS}$

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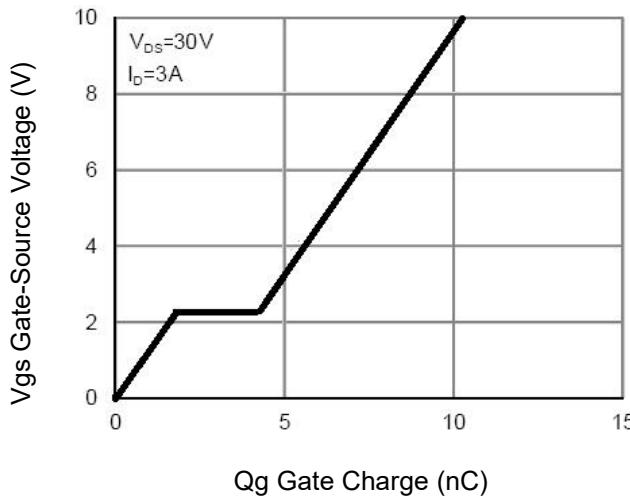


Figure 11 Gate Charge

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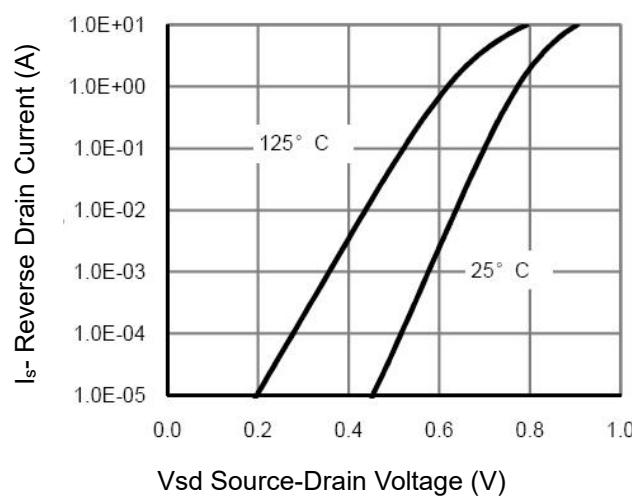
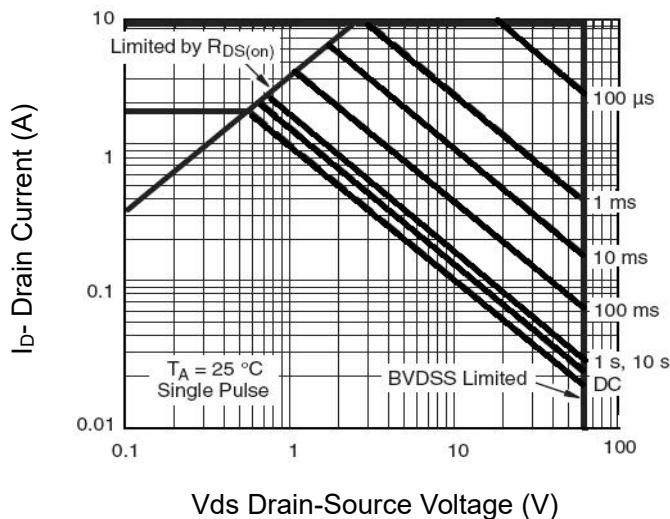


Figure 12 Source-Drain Diode Forward

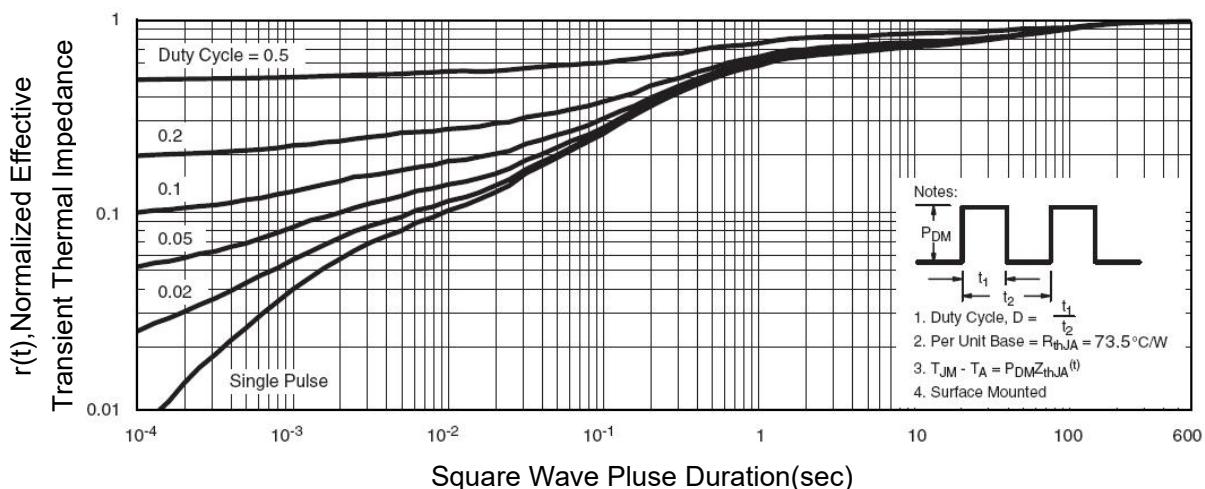
Figure 12 Source-Drain Diode Forward

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**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

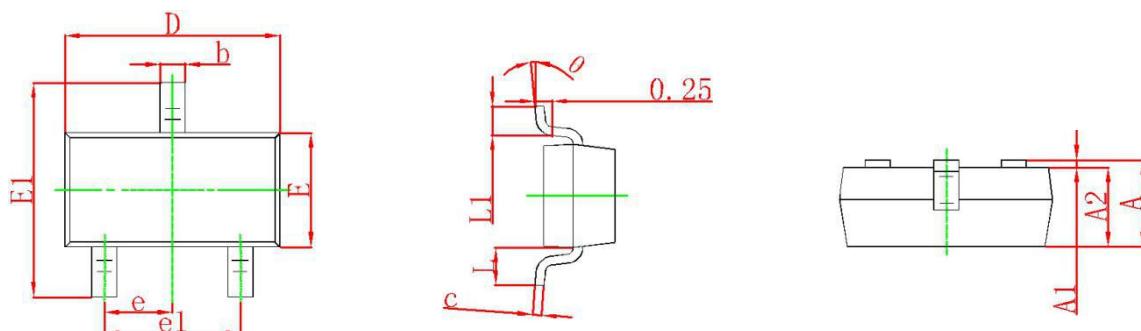


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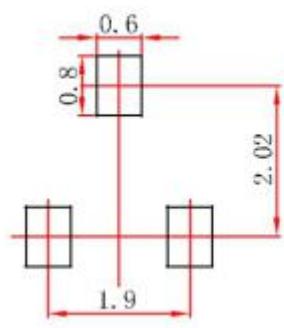
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## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



Note:  
1. Controlling dimension: in millimeters.  
2. General tolerance:  $\pm 0.05\text{mm}$ .  
3. The pad layout is for reference purposes only.